MOSFET – Dual, N-Channel, Small Signal, XLLGA6, 0.65mm x 0.90mm x 0.4mm 20 V, 200 mA

NTND31015NZ

Features

- Dual N-Channel MOSFET
- Offers a Low R_{DS(ON)} Solution in the Ultra Small 0.65 mm x 0.90 mm Package
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

Applications

- Small Signal Load Switch
- Analog Switch
- High Speed Interfacing
- Optimized for Power Management in Ultra Portable Products

MAXIMUM RATINGS ($T_J = 25^{\circ}C$ unless otherwise specified)

Parameter			Symbol	Value	Unit
Drain-to-Source Voltage			V_{DSS}	20	V
Gate-to-Source Voltage			V _{GS}	±8	V
Continuous Drain	Steady State	T _A = 25°C	I _D	200	mA
Current (Note 1)	State	T _A = 85°C		140	
	t ≤ 5 s			220	
Power Dissipation (Note 1)	Steady State	T _A = 25°C	P _D	125	mW
	t ≤ 5 s			166	
Pulsed Drain Current $t_p = 10 \mu s$			I _{DM}	800	mA
Operating Junction and Storage Temperature			T _J , T _{STG}	-55 to 150	°C
Source Current (Body Diode) (Note 2)			Is	200	mA
Lead Temperature for Soldering Purposes (1/8" from case for 10 s)			TL	260	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

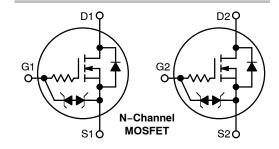
- Surface-mounted on FR4 board using the minimum recommended pad size, 1 oz Cu.
- 2. Pulse Test: pulse width \leq 300 μ s, duty cycle \leq 2%



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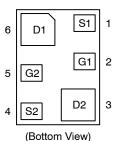
V _{(BR)DSS}	R _{DS(ON)} MAX	I _D Max
20 V	1.5 Ω @ 4.5 V	
	2.0 Ω @ 2.5 V	200 mA
	3.0 Ω @ 1.8 V	200 IIIA
	4.5 Ω @ 1.5 V	





XLLGA6 Case 713AC

PINOUT DIAGRAM



(Dollotti view)

MARKING DIAGRAM



D = Specific Device Code

M = Date Code

ORDERING INFORMATION

See detailed ordering and shipping information on page 2 of this data sheet.

NTND31015NZ

THERMAL RESISTANCE RATINGS

Parameter	Symbol	Мах	Unit	
Junction-to-Ambient - Steady State (Note 3)	Б	998	0000	
Junction-to-Ambient - t ≤ 5 s (Note 3)	$R_{ hetaJA}$	751	°C/W	

^{3.} Surface-mounted on FR4 board using the minimum recommended pad size, 1 oz Cu.

ELECTRICAL CHARACTERISTICS (T₁ = 25°C unless otherwise specified)

Parameter	Symbol	Test Condition		Min	Тур	Max	Unit
OFF CHARACTERISTICS	•			•			
Drain-to-Source Breakdown Voltage	V _{(BR)DSS}	$V_{GS} = 0 \text{ V}, I_D = 250 \mu\text{A}$		20			V
Zero Gate Voltage Drain Current		V _{GS} = 0 V, V _{DS} = 5 V	T _J = 25°C			50	nA
	I _{DSS}		T _J = 85°C			200	- 4
		V _{GS} = 0 V, V _{DS} = 16 V	T _J = 25°C			100	nA
Gate-to-Source Leakage Current	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 5.0 \text{ V}$				±100	nA
ON CHARACTERISTICS (Note 4)							
Gate Threshold Voltage	V _{GS(TH)}	$V_{GS} = V_{DS}, I_D = 2$	250 μΑ	0.4		1.0	V
Drain-to-Source On Resistance		$V_{GS} = 4.5 \text{ V}, I_D = 100 \text{ mA}$			0.8	1.5	Ω
		$V_{GS} = 2.5 \text{ V}, I_D = 50 \text{ mA}$			1.1	2.0	
	R _{DS(ON)}	V _{GS} = 1.8 V, I _D = 20 mA			1.4	3.0	
		V _{GS} = 1.5 V, I _D = 10 mA			1.8	4.5	
Forward Transconductance	9FS	V _{DS} = 5.0 V, I _D = 125 mA			0.48		S
Forward Diode Voltage	V_{SD}	V _{GS} = 0 V, I _S = 10 mA			0.6	1.0	>
CAPACITANCES							
Input Capacitance	C _{ISS}	f = 1 MHz, V _{GS} = 0 V V _{DS} = 15 V			12.3		pF
Output Capacitance	C _{OSS}				3.4		
Reverse Transfer Capacitance	C _{RSS}				2.5		
SWITCHING CHARACTERISTICS, $V_{GS} =$	4.5 V (Note 4)						
Turn-On Delay Time	t _{d(ON)}	V_{GS} = 4.5 V, V_{DD} = 10 V, I_{D} = 200 mA, R_{G} = 3 Ω			16.5		- ns
Rise Time	t _r				25.5		
Turn-Off Delay Time	t _{d(OFF)}				142		
Fall Time	t _f				80		

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

ORDERING INFORMATION

Device	Package	Shipping [†]
NTND31015NZTAG	XLLGA6 (Pb-Free)	8000 / Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

^{4.} Switching characteristics are independent of operating junction temperatures.

NTND31015NZ

TYPICAL CHARACTERISTICS

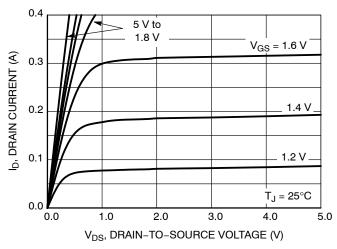


Figure 1. On-Region Characteristics

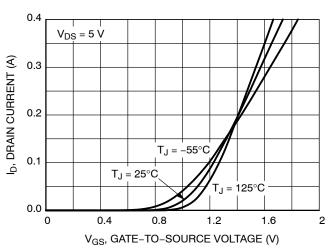


Figure 2. Transfer Characteristics

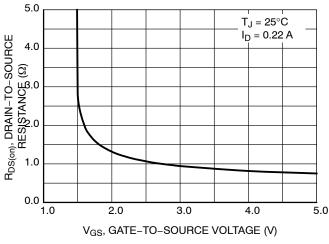


Figure 3. On-Resistance vs. Gate-to-Source Voltage

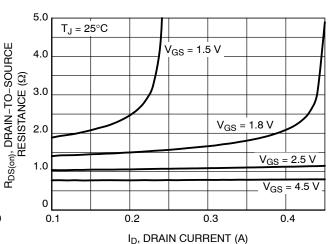


Figure 4. On-Resistance vs. Drain Current and Gate Voltage

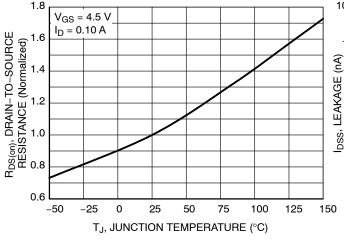


Figure 5. On–Resistance Variation with Temperature

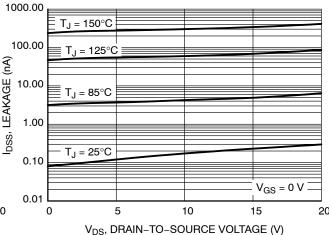
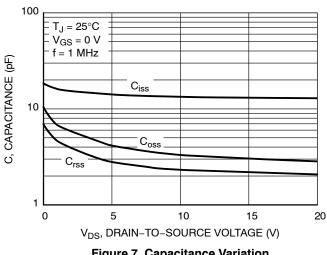


Figure 6. Drain-to-Source Leakage Current vs. Voltage

NTND31015NZ

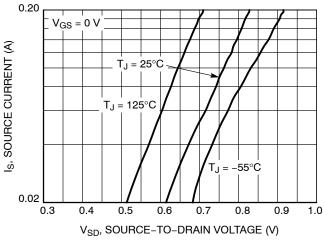
TYPICAL CHARACTERISTICS



 $V_{DS} = 10 V$ $I_D = 0.2 \text{ A}, V_{GS} = 4.5 \text{ V}$ t_{d(off)} 100 t, TIME (ns) t_{r} t_{d(on)} 10 10 100 R_G , GATE RESISTANCE (Ω)

Figure 7. Capacitance Variation

Figure 8. Resistive Switching Time Variation vs. Gate Resistance



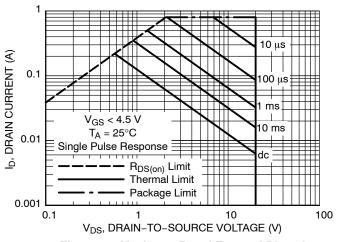
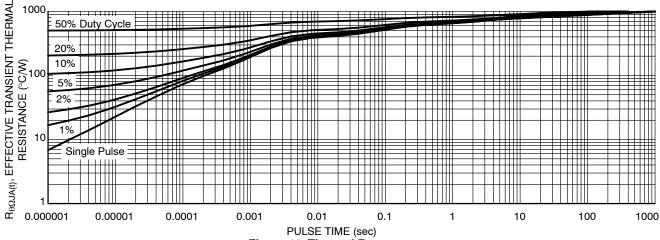


Figure 9. Diode Forward Voltage vs. Current

Figure 10. Maximum Rated Forward Biased Safe Operating Area

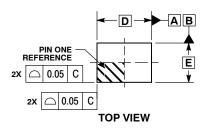


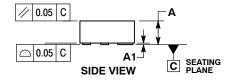


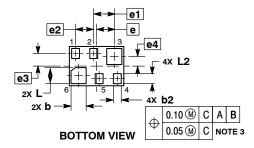


XLLGA6 0.90x0.65 CASE 713AC ISSUE O

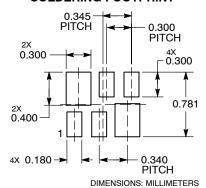
DATE 19 JUN 2014







RECOMMENDED SOLDERING FOOTPRINT*



*For additional information on our Pb-Free strategy and soldering details, please download the onsemi Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

NOTES:

- NOTES:

 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.

 2. CONTROLLING DIMENSION: MILLIMETERS.

 3. POSITIONAL TOERANCE APPLIES TO ALL
- SIX LEADS.

	MILLIMETERS				
DIM	MIN	MAX			
Α	0.340	0.440			
A1	0.000	0.050			
b	0.200	0.300			
b2	0.080	0.180			
D	0.900	0.900 BSC			
E	0.650 BSC				
е	0.295 BSC				
e1	0.340 BSC				
e2	0.300 BSC				
е3	0.208 BSC				
e4	0.158 BSC				
L	0.215	0.315			
L2	0.115	0.215			

GENERIC MARKING DIAGRAM*



= Specific Device Code

Μ = Date Code

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot " ■", may or may not be present.

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